

AMENDMENT TO THE CLAIMS

The following clean set of claims is presented in accordance with 37 C.F.R. 1.121 and by making this submission any claim not indicated as currently amended is asserted not to be changed relative to the immediate prior version of the claim.

1. (Canceled)
2. (Previously presented) A method for manufacturing a semiconductor device comprising the step of:
forming an insulating film comprising silicon nitride over a semiconductor by sputtering in an atmosphere comprising nitrogen at 75 volume % or more.
3. (Previously Presented) A method according to claim 2 wherein the sputtering is performed by an RF sputtering method.
4. (Previously Presented) A method according to claim 2 wherein the semiconductor device is incorporated into an active matrix display device.
5. (Previously presented) A method for manufacturing a semiconductor device comprising the step of:
forming an insulating film comprising silicon nitride over a semiconductor by sputtering in an atmosphere comprising nitrogen at 75 volume % or more and argon at 25 volume % or less.
6. (Previously Presented) A method according to claim 5 wherein the sputtering is performed by an RF sputtering method.
7. (Previously Presented) A method according to claim 5 wherein the semiconductor device is incorporated into an active matrix display device.

8. (Previously presented) A method according to claim 5 wherein the atmosphere further comprises halogen at 0.2 to 20 volume %

9. (Previously presented) A method for manufacturing a semiconductor device comprising the steps of:

forming an insulating film comprising silicon nitride over a semiconductor by sputtering in an atmosphere comprising nitrogen at 75 volume % or more; and

forming an electrode comprising aluminum over the insulating film.

10. (Previously Presented) A method according to claim 9 wherein the sputtering is performed by an RF sputtering method.

11. (Previously Presented) A method according to claim 9 wherein the semiconductor device is incorporated into an active matrix display device.

12. (Previously presented) A method for manufacturing a semiconductor device comprising the steps of:

forming an insulating film comprising silicon nitride over a semiconductor by sputtering in an atmosphere comprising nitrogen at 75 volume % or more and argon at 25 volume % or less; and

forming an electrode comprising aluminum over the insulating film.

13. (Previously Presented) A method according to claim 12 wherein the sputtering is performed by an RF sputtering method.

14. (Previously Presented) A method according to claim 12 wherein the semiconductor device is incorporated into an active matrix display device.

15. (Previously presented) A method according to claim 12 wherein the atmosphere further comprises halogen at 0.2 to 20 volume %.

16. (Previously presented) A method for manufacturing a semiconductor device comprising the step of:

forming a transistor; and

forming an insulating film comprising silicon nitride over the transistor by sputtering in an atmosphere comprising nitrogen at 75 volume % or more.

17. (Previously Presented) A method according to claim 16 wherein the sputtering is performed by an RF sputtering method.

18. (Previously Presented) A method according to claim 16 wherein the semiconductor device is incorporated into an active matrix display device.

19. (Previously presented) A method for manufacturing a semiconductor device comprising the step of:

forming a transistor; and

forming an insulating film comprising silicon nitride over the transistor by sputtering in an atmosphere comprising nitrogen at 75 volume % or more and argon at 25 volume % or less.

20. (Previously Presented) A method according to claim 19 wherein the sputtering is performed by an RF sputtering method.

21. (Previously Presented) A method according to claim 19 wherein the semiconductor device is incorporated into an active matrix display device.

22. (Previously presented) A method according to claim 19 wherein the atmosphere further comprises halogen at 0.2 to 20 volume %.